

Silicon Standard Recovery Diode

$V_{RRM} = 50 \text{ V} - 1000 \text{ V}$

$I_F = 35 \text{ A}$

Features

- High Surge Capability
- Types up to 1000 V V_{RRM}

DO-5 Package



Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N1183 (R)	1N1184 (R)	1N1186 (R)	1N1187 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	300	V
RMS reverse voltage	V_{RMS}		35	70	140	210	V
DC blocking voltage	V_{DC}		50	100	200	300	V
Continuous forward current	I_F	$T_C \leq 140^\circ\text{C}$	35	35	35	35	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	595	595	595	595	A
Operating temperature	T_j		-65 to 190	-65 to 190	-65 to 190	-65 to 190	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N1183 (R)	1N1184 (R)	1N1186 (R)	1N1187 (R)	Unit
Diode forward voltage	V_F	$I_F = 35 \text{ A}$, $T_j = 25^\circ\text{C}$	1.2	1.2	1.2	1.2	V
Reverse current	I_R	$V_R = 50 \text{ V}$, $T_j = 25^\circ\text{C}$	10	10	10	10	μA
		$V_R = 50 \text{ V}$, $T_j = 140^\circ\text{C}$	10	10	10	10	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.25	0.25	0.25	0.25	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

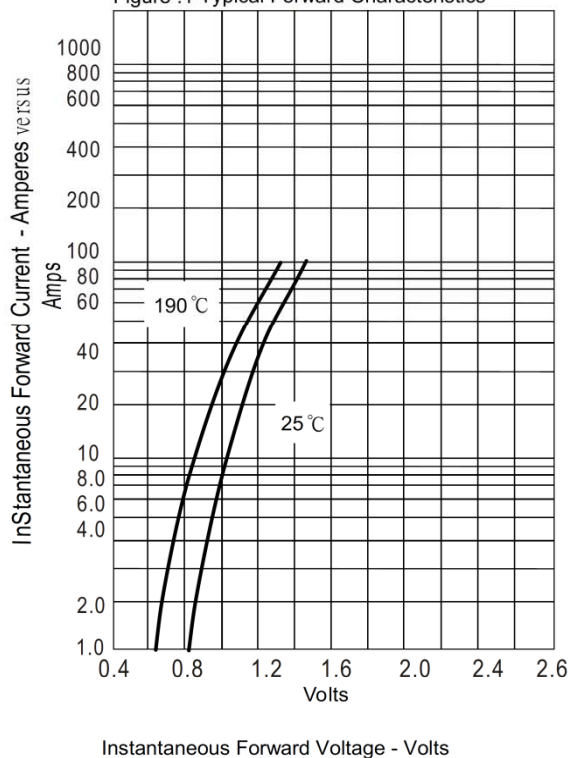


Figure .2-Forward Derating Curve

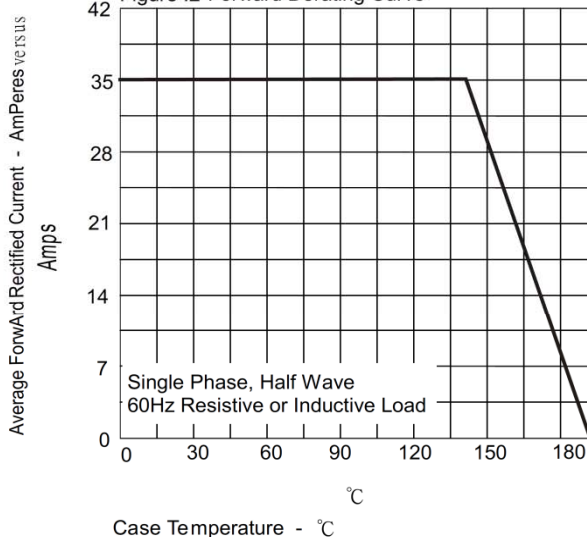
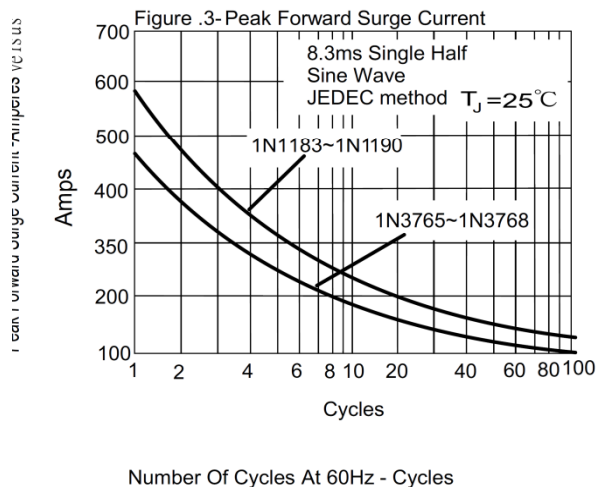
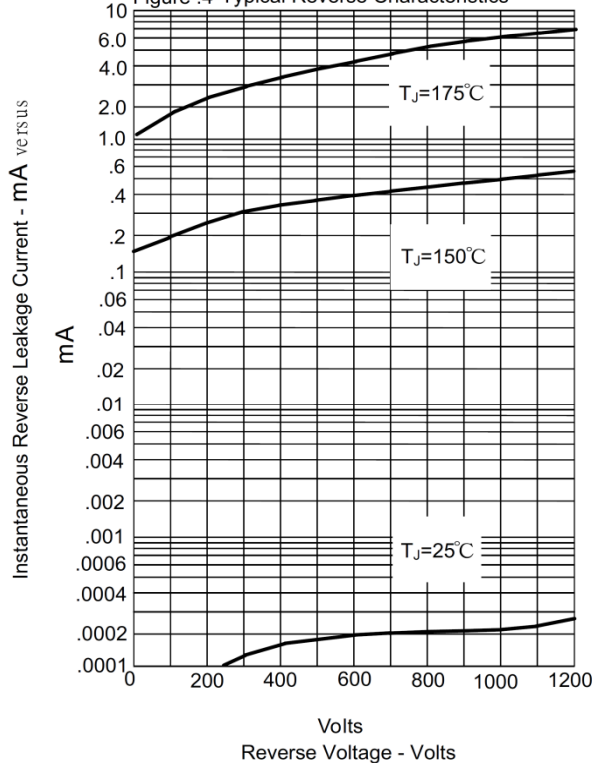


Figure .4-Typical Reverse Characteristics



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